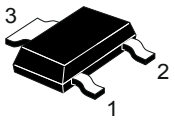
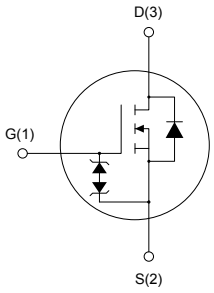
N-channel 600 V, 1.00 Ω typ., 5.5 A MDmesh M2 Power MOSFET in an SOT223-2 package



SOT223-2



NG1D3S2_SOT223

Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STN6N60M2	600 V	1.25 Ω	5.5 A

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Product status link
STN6N60M2

Product summary	
Order code	STN6N60M2
Marking	6N60M2
Package	SOT223-2
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D (1)	Drain current (continuous) at T_C = 25 °C	5.5	A
I_D (1)	Drain current (continuous) at T_C = 100 °C	3.5	A
I_{DM} (2)	Drain current (pulsed)	8	A
P_{TOT}	Total power dissipation at T_S = 25 °C	6	W
dv/dt(3)	Peak diode recovery voltage slope	15	V/ns
dv/dt(4)	MOSFET dv/dt ruggedness	50	
T_J	Operating junction temperature range	-55 to 150	°C
T_{stg}	Storage temperature range		

1. *Limited by maximum junction temperature.*
2. *Pulse width limited by safe operating area.*
3. *I_{SD} ≤ 5.5 A, di/dt = 400 A/µs; $V_{DS(peak)}$ < $V_{(BR)DSS}$, V_{DD} = 400 V*
4. *V_{DS} ≤ 480 V*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}S}$	Thermal resistance junction-solder point	20	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb	38	°C/W

1. *When mounted on 1 inch² FR-4, 2 Oz copper board.*

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax.}$)	0.8	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	83	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 4. On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS}= 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			1	µA
		V_{GS} = 0 V, V_{DS} = 600 V; T_C = 125 °C (1)			100	µA
I_{GSS}	Gate body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 2 A		1.00	1.25	Ω

1. *Defined by design, not subject to production test.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	220	-	pF
C_{oss}	Output capacitance		-	12.5	-	pF
C_{rss}	Reverse transfer capacitance		-	3.3	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	23	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D=0 A	-	9	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 4 A, V_{GS} = 0 to 10 V, (see Figure 15. Test circuit for gate charge behavior)	-	6.2	-	nC
Q_{gs}	Gate-source charge		-	1.3	-	nC
Q_{gd}	Gate-drain charge		-	2.7	-	nC

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 2 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 14. Test circuit for resistive load switching times and Figure 19. Switching time waveform)	-	6.4	-	ns
t_r	Rise time		-	6.2	-	ns
$t_{d(off)}$	Turn-off delay time		-	18	-	ns
t_f	Fall time		-	15.8	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} (1)	Source-drain current		-		5.5	A
I_{SDM} (2)	Source-drain current (pulsed)		-		8	A
V_{SD} (3)	Forward on voltage	I_{SD} = 4 A, V_{GS} = 0 V	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 4 A, di/dt = 100 A/µs, V_{DD} = 60 V, (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	229		ns
Q_{rr}	Reverse recovery charge		-	721		nC
I_{RRM}	Reverse recovery current		-	6.3		A
t_{rr}	Reverse recovery time	I_{SD} = 4 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	288		ns
Q_{rr}	Reverse recovery charge		-	936		nC
I_{RRM}	Reverse recovery current		-	6.5		A

1. *Limited by maximum junction temperature.*
2. *Pulse width limited by safe operating area.*
3. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

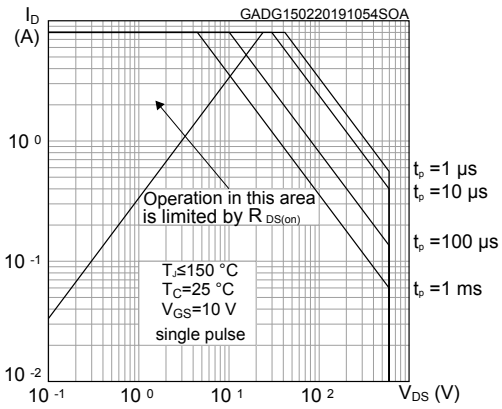


Figure 2. Thermal impedance

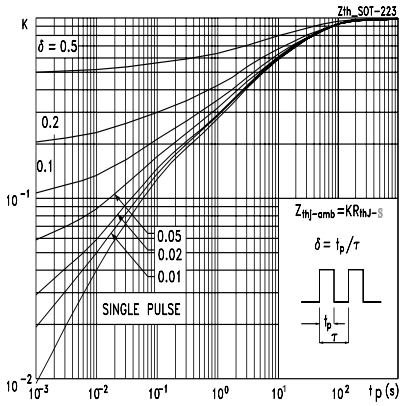


Figure 3. Output characteristics

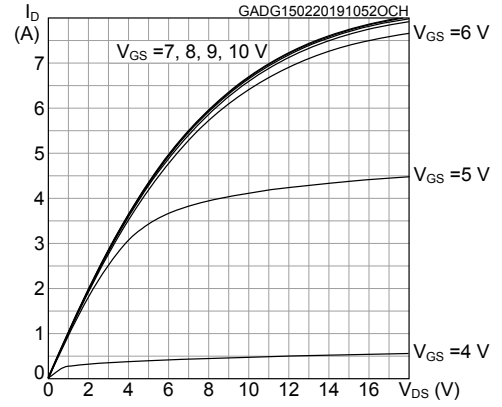


Figure 4. Transfer characteristics

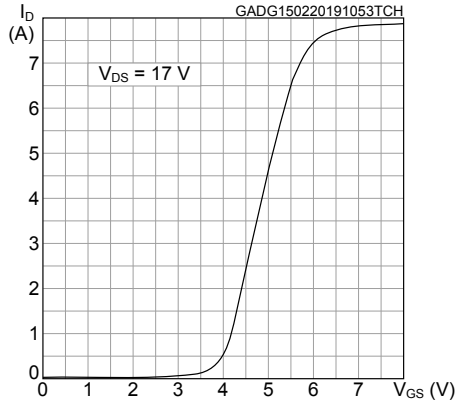


Figure 5. Normalized $V_{BR(DSS)}$ vs temperature

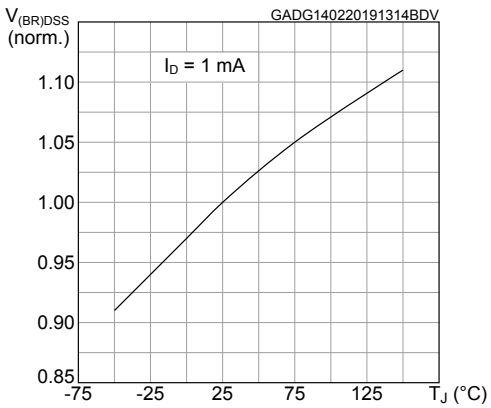


Figure 6. Static drain-source on-resistance

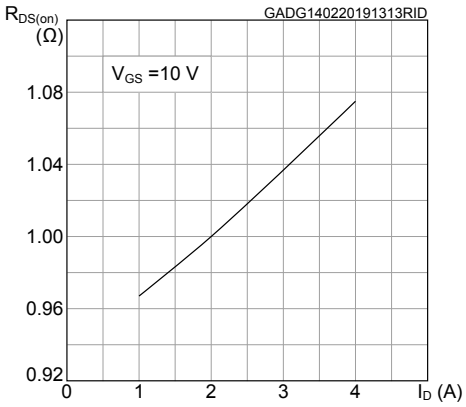


Figure 7. Gate charge vs gate-source voltage

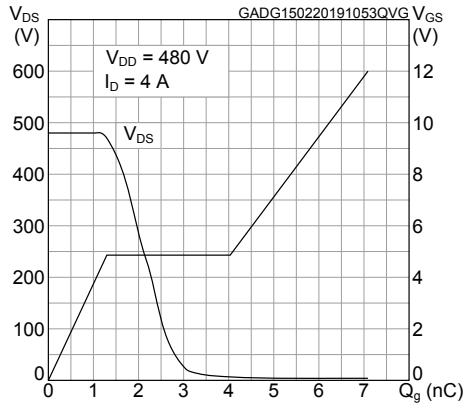


Figure 8. Capacitance variations

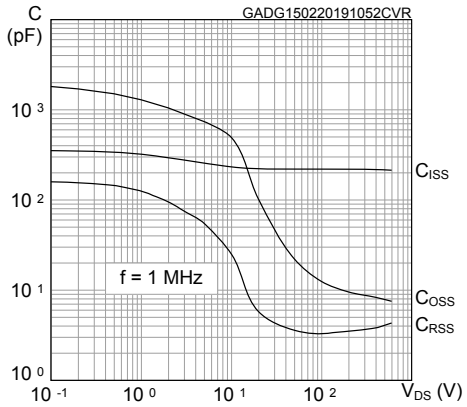


Figure 9. Normalized gate threshold voltage vs temperature

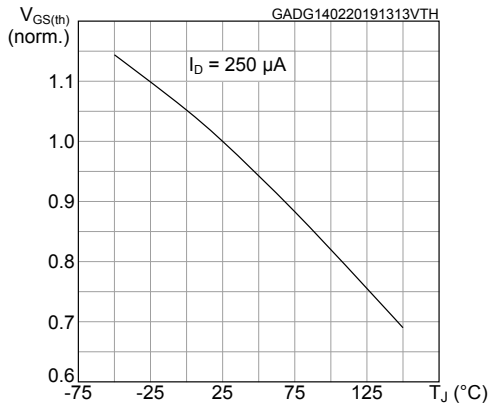


Figure 10. Normalized on-resistance vs temperature

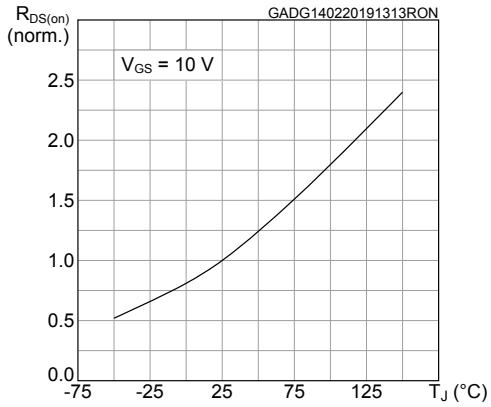


Figure 11. Source-drain diode forward characteristics

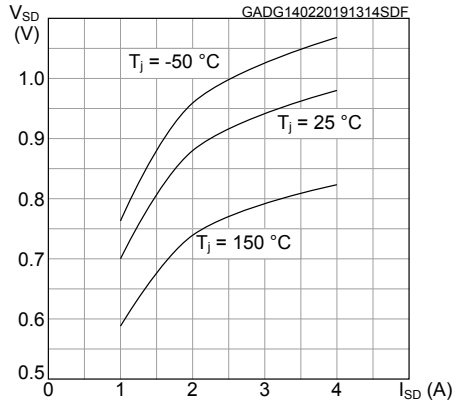
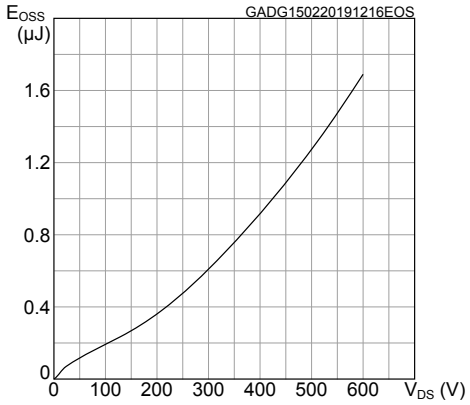


Figure 12. Output capacitance stored energy



3 Test circuits

Figure 13. Test circuit for resistive load switching times

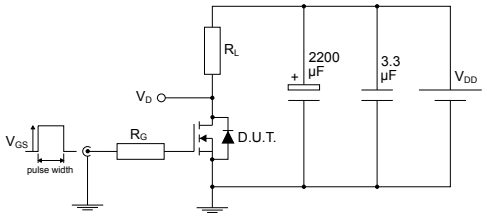


Figure 14. Test circuit for gate charge behavior

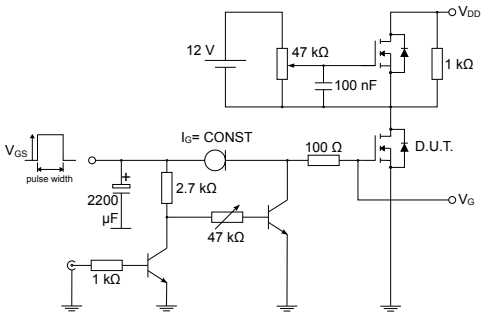


Figure 15. Test circuit for inductive load switching and diode recovery times

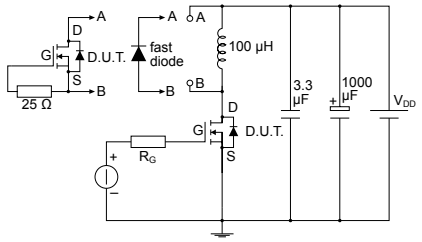


Figure 16. Unclamped inductive load test circuit

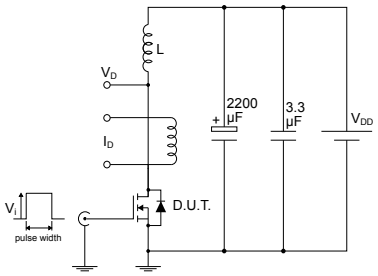


Figure 17. Unclamped inductive waveform

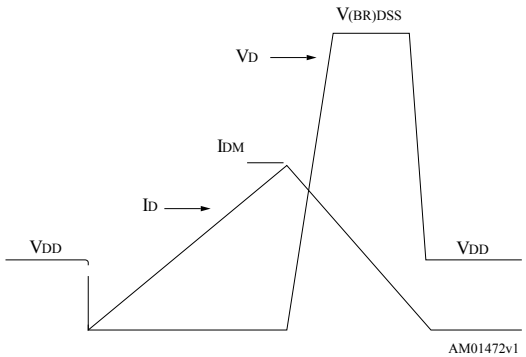
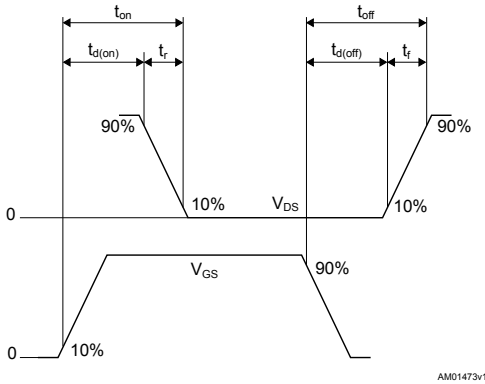


Figure 18. Switching time waveform

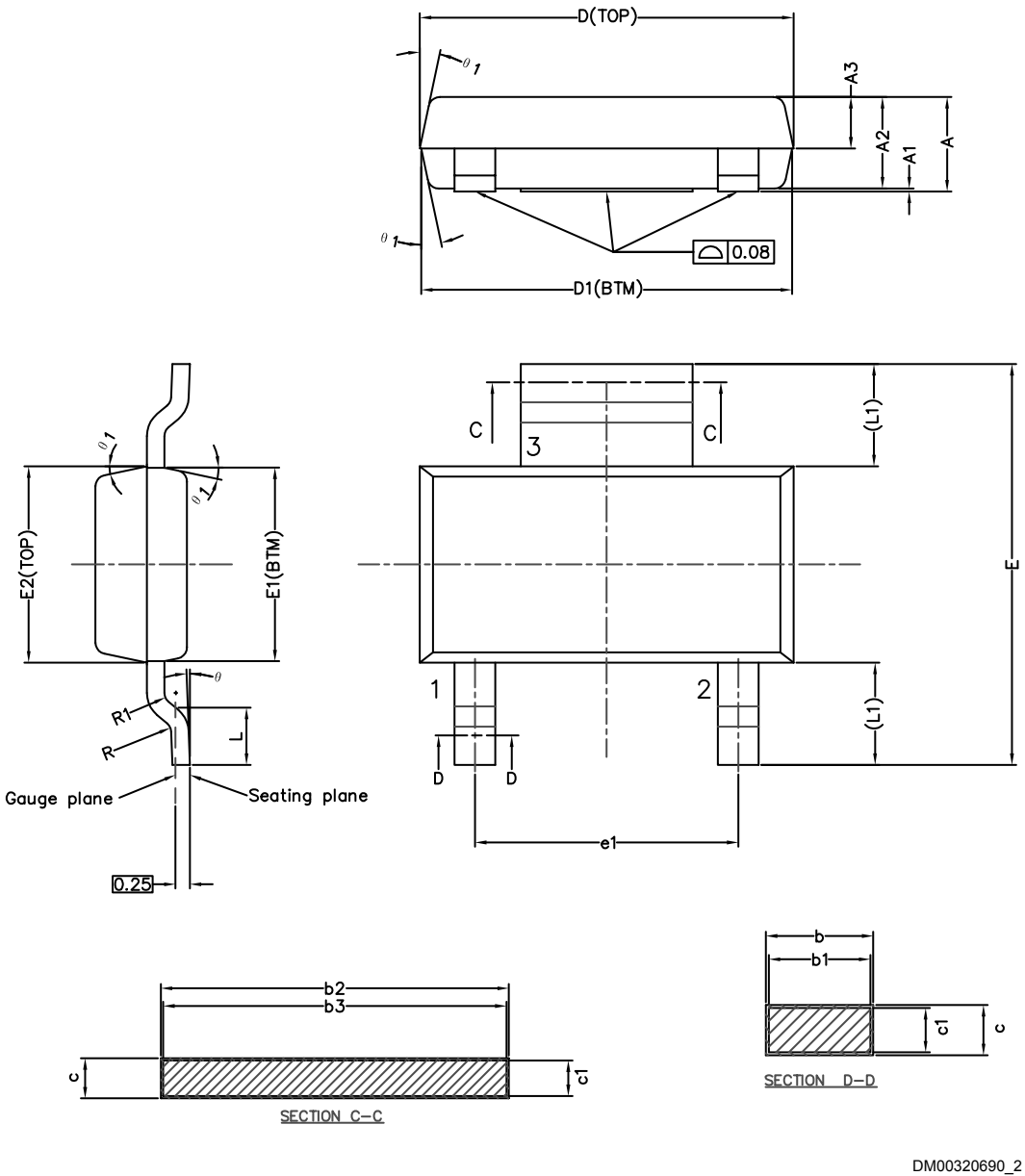


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 SOT223-2 package information

Figure 19. **SOT223-2 package outline**

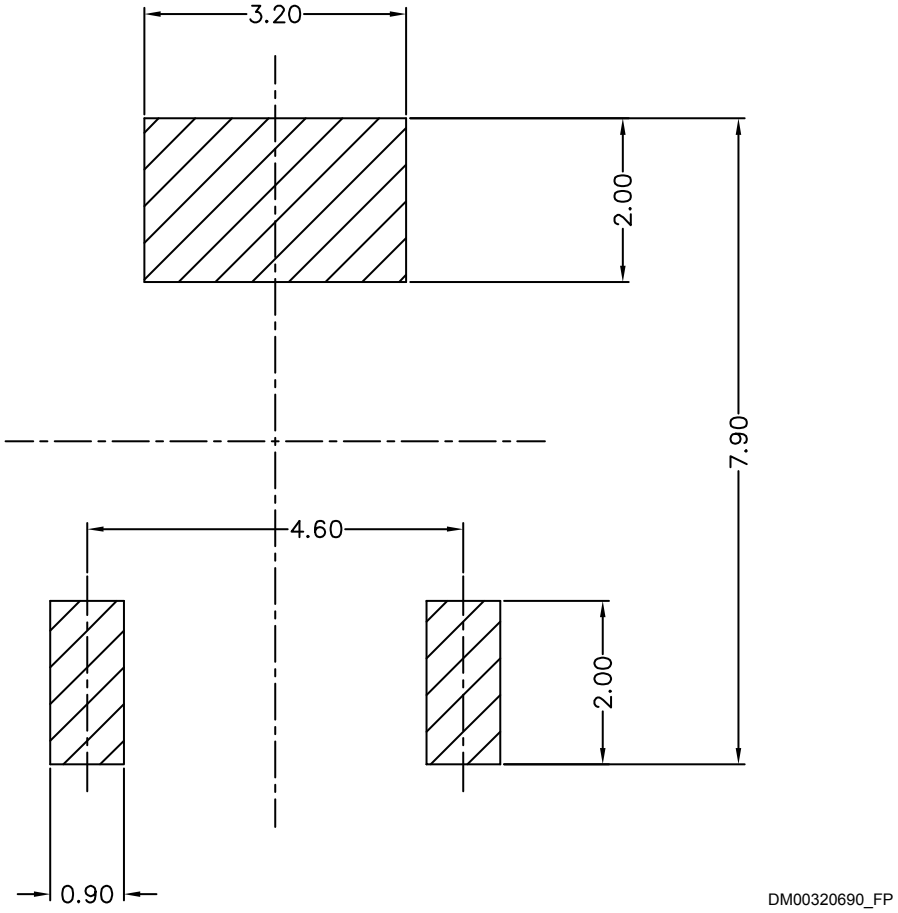


DM00320690_2

Table 8. **SOT223-2 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A			1.80
A1	0.02		0.10
A2	1.50	1.60	1.70
A3	0.80	0.90	1.00
b	0.67		0.80
b1	0.66	0.71	0.76
b2	2.96		3.09
b3	2.95	3.00	3.05
c	0.30		0.35
c1	0.29	0.30	0.31
D	6.48	6.53	6.58
D1	6.43	6.48	6.53
E	6.80		7.20
E1	3.30	3.38	3.48
E2	3.33	3.43	3.53
e1	4.50	4.60	4.70
L	0.80	1.00	1.20
L1		1.78 REF	
R	0.10		
R1	0.10		
θ	0°		8°
θ_1	10°	12°	14°

Figure 20. **SOT223-2 recommended footprint (dimensions are in mm)**



Revision history

Table 9. **Document revision history**

Date	Revision	Changes
18-Feb-2019	1	First release.
21-May-2020	2	Updated Table 1. Absolute maximum ratings and Table 7. Source-drain diode.

Contents

Mouser Electronics

Authorized Distributor

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STMicroelectronics:

STN6N60M2